

**Erratum: "Ellipsometric characterization of  $\text{In}_{0.52}\text{Al}_{0.48}\text{As}$  and of modulation doped field effect transistor structures on InP substrates" [Appl. Phys. Lett. 62, 1411 (1993)]**

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The caption for Table II showed a wrong analysis wavelength range 300–405 nm.

The correct caption for Table II is:

Table II. Best fits for  $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}/\text{In}_{0.52}\text{Al}_{0.48}\text{As}$  MODFET layer thicknesses (in nm). Analysis wavelength range 300–540 nm. 400 nm  $\text{In}_{0.52}\text{Al}_{0.48}\text{As}$  layer used as substrate.